



## STATIC AND DYNAMIC PROPERTIES OF AMORPHOUS MATERIAL DERIVED FROM ZEOLITE ZSM-5

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### Introduction

#### Motivation

Study of zeolite-based amorphous materials are important for technological applications:

- **Catalysis** [1]
- **Ion-exchange** [2]
- **Ceramic Chemistry** [3]

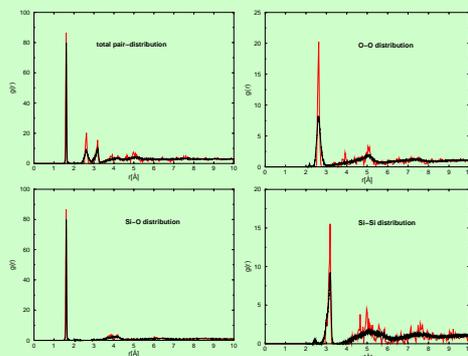
#### Method

- **Molecular dynamics** using **BKS interaction potentials** [4] with **canonical ensembling**.

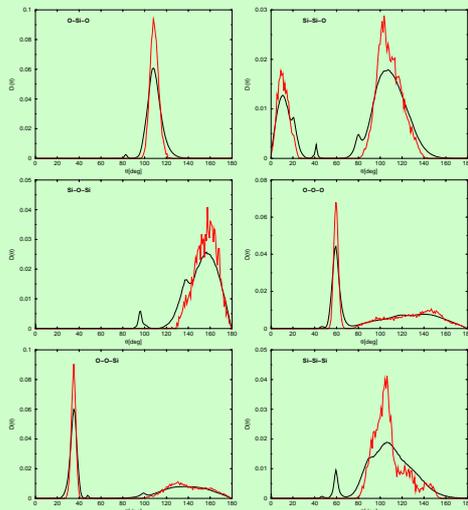
### Results

#### Static Properties [5]

##### Pair-distribution functions



##### Bond angle distributions



(Red line for crystalline ZSM-5 and black line for the amorphous form derived from it).

- Slightly distorted SiO<sub>4</sub> tetrahedra are the basic units.
- Connectivity: Mainly corner sharing and a

### References

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 [2] B. X. Gu, L. M. Wang, R. C. Ewing, J. Nucl. Mater. **278**, 64, 2000  
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 [4] G. J. Kramer, N. P. Farragher, B. W. H. van Beest, R. A. van

Santen, Phys. Rev. B **43**, 5068, 1991  
 [5] A. B. Mukhopadhyay, C. Oligschleger, M. Dolg, Phys. Rev. B **67**, 14106, 2003  
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### Acknowledgement

The financial support by the Deutsche Forschungsgemeinschaft is gratefully acknowledged.

- **System size:** 3456 and 1152 atoms for static and dynamic properties, respectively.
- **Structure generation:** Silicious crystalline configuration was heated to temperatures  $T = 4700$  K, 4800 K, 4900 K and 5000 K, then equilibrated and finally quenched to  $T = 300$  K followed by equilibration of  $3 \times 10^5$  time steps with each **time step** of 2 fs.
- Stored expected minima were quenched to zero temperature using a combined **steepest-**

**descent-conjugate-gradient algorithm** and used for analysis of structural and vibrational properties.

- Extent of amorphization was quantified as **percentage of energy crystallinity (PEC)** [5], i.e.,

$$PEC = \frac{E_{amorphous} - E_{configuration}}{E_{amorphous} - E_{crystalline}} \times 100$$

- $E_{amorphous} = -16.9$  eV/atom represents the energy per atom of the maximum amorphized structure obtained in our simulation.

small percentage of **edge sharing** were observed.

##### Internal surface area (ISA)

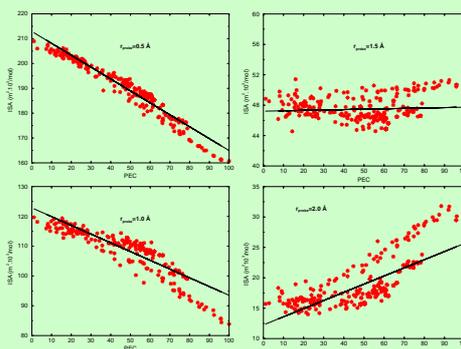
- We model the system as an ensemble of intersecting hard spheres with radii depending on the coordination number (CN).

Atomic/ionic radii  $R_{coord}$  (in Å) for O and Si.

CN	$R_{coord}(O)$	$R_{coord}(Si)$
0	1.52	2.10
1	1.435	1.64
2	1.35	1.18
3	0	0.72
4	0	0.26
5 and higher	0	0

- ISA was determined using the **probe-atom model**.

$$ISA = \frac{1}{M} \left( \sum_{i=1}^N 4\pi [R_{coord}(i) + r_{probe}]^2 \frac{P_i}{p} \right)$$



- Effect of amorphization for:

**Large probe radii:** ISA decreases due to the reduction in the number of large pores.

**Small probe radii:** ISA increases due to increase in under-coordination and increasing

tendency to convert large rings into smaller rings.

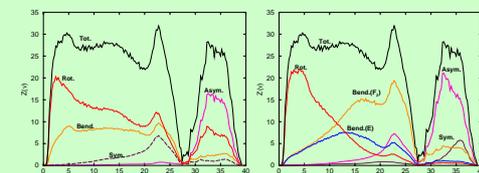
##### Dynamic Properties [6]

##### Relative contribution of motions of structural subunits to vibrational density of states (VDOS)

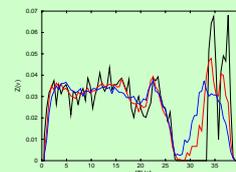
- VDOS were obtained by diagonalization of the dynamic matrix.

- Two basic subunits Si-O-Si and SiO<sub>4</sub> with the approximate local point group symmetries  $C_{2v}$  and  $T_d$ , respectively, were considered.

- In order to investigate atomic motions for different eigenmodes, projections of eigenvectors onto the various vibrational modes of structural subunits were performed.



(a) Si-O-Si (b) SiO<sub>4</sub>  
 Effect of extent of amorphization on VDOS



(Black line refers to the VDOS for the crystalline ZSM-5 and the red line for the structures with PEC of 70 % and the blue line for the structures with PEC of 50 %).

- Amorphization leads to broadening of high-frequency peaks and shifts peaks towards low frequency with a narrowing of the band gap.